

SPECIFICATION OF LED CHIP C940-40P [INFRARED]

1) Commodity Type and Physical Characteristics.

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|----------------------|-------------|------------------|------------|
| 1. Material | GaAlAs/GaAs | | |
| 2. Electrode | Top Side | P (anode) side | : Au Alloy |
| | Bottom Side | N (cathode) side | : Au Alloy |
| 3. Electrode Pattern | Fig.1 | | |
| 4. Chip Size | Fig.2 | | |
| 5. Chip Thickness | Fig.2 | | |
| 6. Emission Area | Fig.2 | | |

2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.25	1.35	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	2.0	3.5		mW
Peak Wavelength	λ_P	If=20mA	930	940	955	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	If=20mA		50		nm
RiseTime	tr	If=20mA		1000		ns
FallTime	tf	If=20mA		500		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.(Ta=25°C)

[Unit : um]

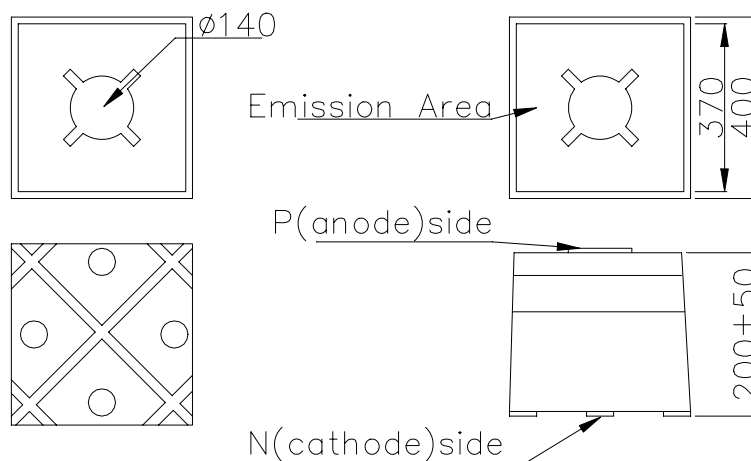


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area